



## PRODUCT DATA SHEET



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**Datasheet**



**Resources**

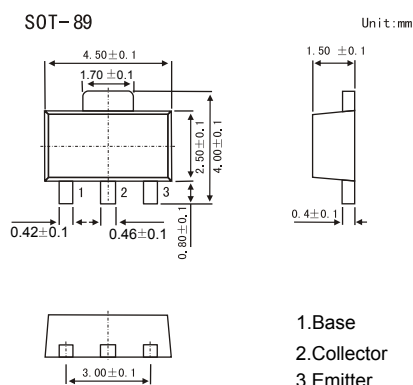


**Samples**

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.jg-semi.cn](http://www.jg-semi.cn). Please email any questions regarding the system integration to [JINGAO\\_questions@jgsemi.com](mailto:JINGAO_questions@jgsemi.com).

### ■ Features

- Low noise and high gain
- High power gain
- Large  $P_{tot}$



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	20	V
Collector - Emitter Voltage	$V_{CE0}$	12	
Emitter - Base Voltage	$V_{EB0}$	3	
Collector Current - Continuous	$I_C$	100	mA
Collector Power Dissipation	$P_C$	1.2	W
Junction to Ambient Resistance	$R_{th(j-a)}$	62.5	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

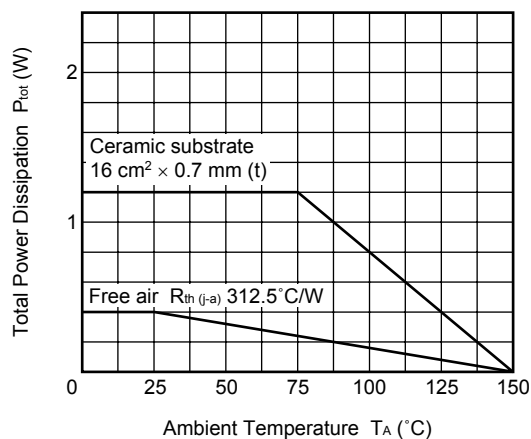
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = 100 \mu\text{A}, I_E = 0$	20			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = 1 \text{ mA}, I_B = 0$	12			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = 100 \mu\text{A}, I_C = 0$	3			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = 20\text{V}, I_E = 0$			1	uA
Emitter cut-off current	$I_{EB0}$	$V_{EB} = 3\text{V}, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.2	
DC current gain (Note.1)	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}$	50		250	
Insertion Power Gain	$ S_{21e} ^2$	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}, f = 1 \text{ GHz}$		9		dB
Noise Figure	NF	$V_{CE} = 10\text{V}, I_C = 7 \text{ mA}, f = 1 \text{ GHz}$		1.1		
		$V_{CE} = 10\text{V}, I_C = 40 \text{ mA}, f = 1 \text{ GHz}$		1.8	3	
Reverse Transfer Capacitance	$C_{re}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1 \text{ MHz}$			1	pF
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}$		6.5		GHz

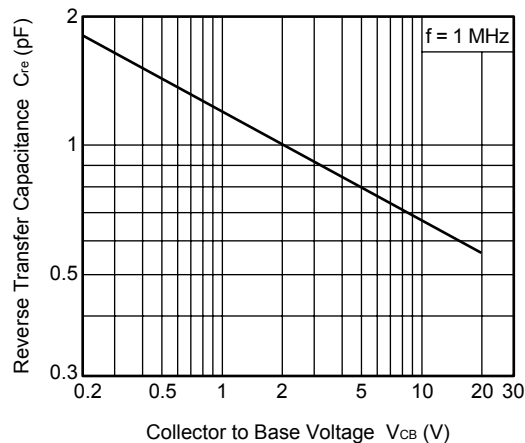
Note.1: Pulse measurement:  $PW \leq 350 \mu\text{s}$ , Duty Cycle  $\leq 2\%$

# ■ Typical Characteristics

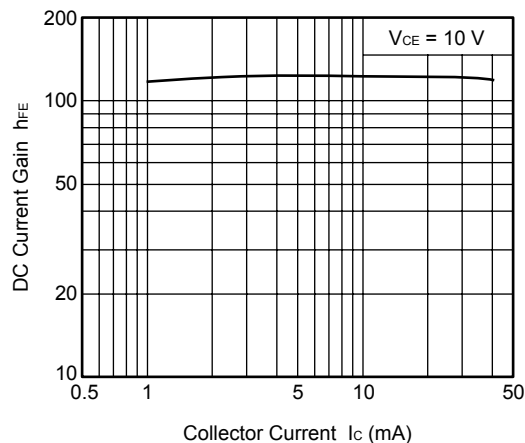
TOTAL POWER DISSIPATION  
vs. AMBIENT TEMPERATURE



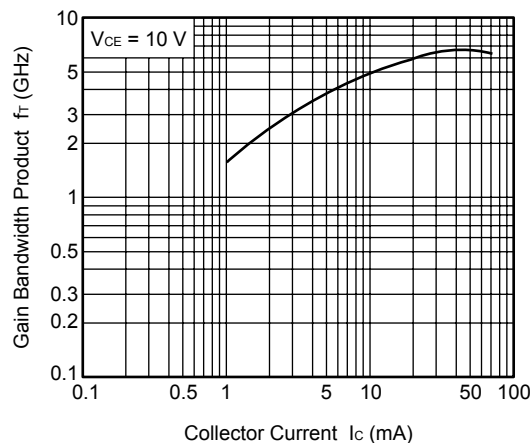
REVERSE TRANSFER CAPACITANCE  
vs. COLLECTOR TO BASE VOLTAGE



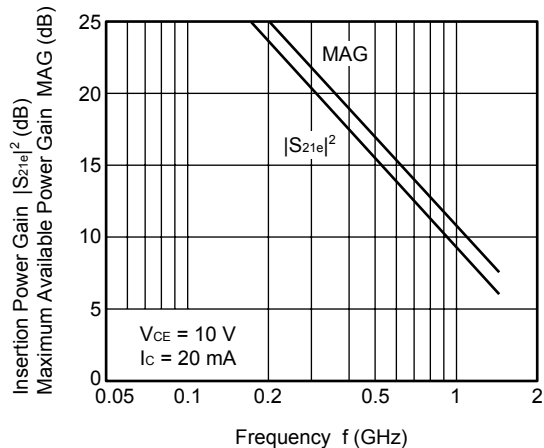
DC CURRENT GAIN vs.  
COLLECTOR CURRENT



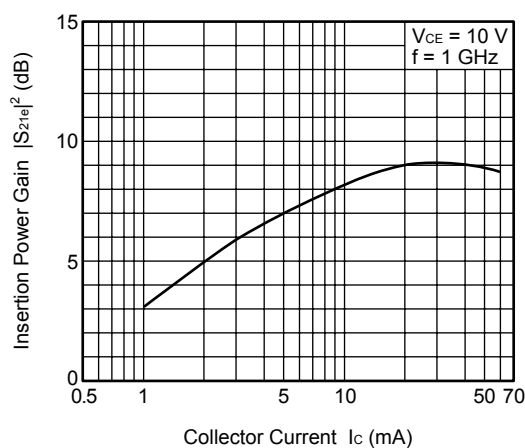
GAIN BANDWIDTH PRODUCT  
vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG  
vs. FREQUENCY

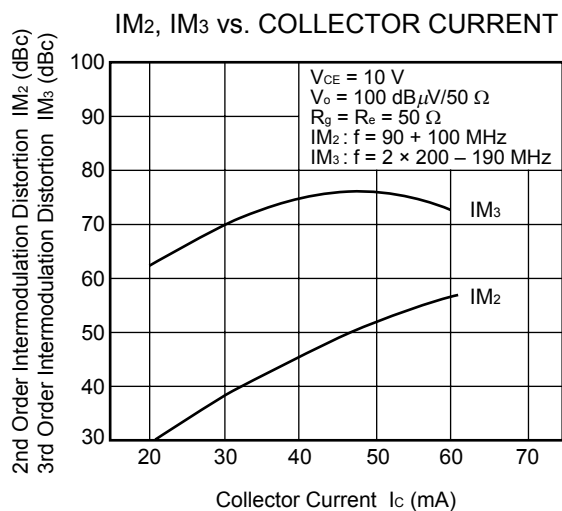
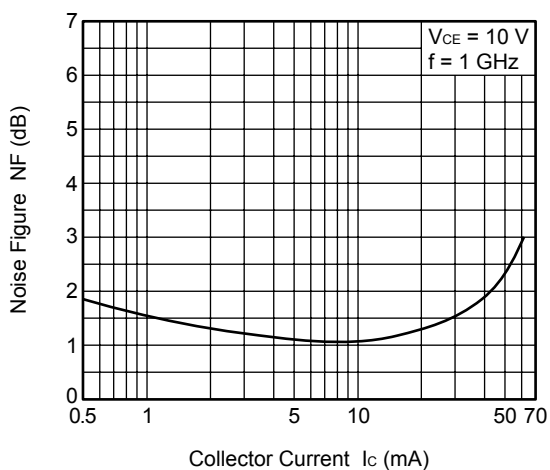


INSERTION POWER GAIN  
vs. COLLECTOR CURRENT



■ Typical Characteristics

NOISE FIGURE vs.  
COLLECTOR CURRENT



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